

FEATURES

- Transistor Optocoupler in SOT223 Package
- End Stackable, 1.27 mm Spacing
- Low Current Input
- Very High CTR, 150% Typical at $I_F=1$ mA, $V_{CE}=0.5$ V
- Good CTR Linearity Versus Forward Current
- Minor CTR Degradation
- Field Effect Stable by TRIOS® (TRANSPARENT IOn Shield)
- High Collector-Emitter Voltage, $V_{CEO}=70$ V
- Low Coupling Capacitance
- High Common Mode Transient Immunity
- Isolation Test Voltage: 2500 VDC

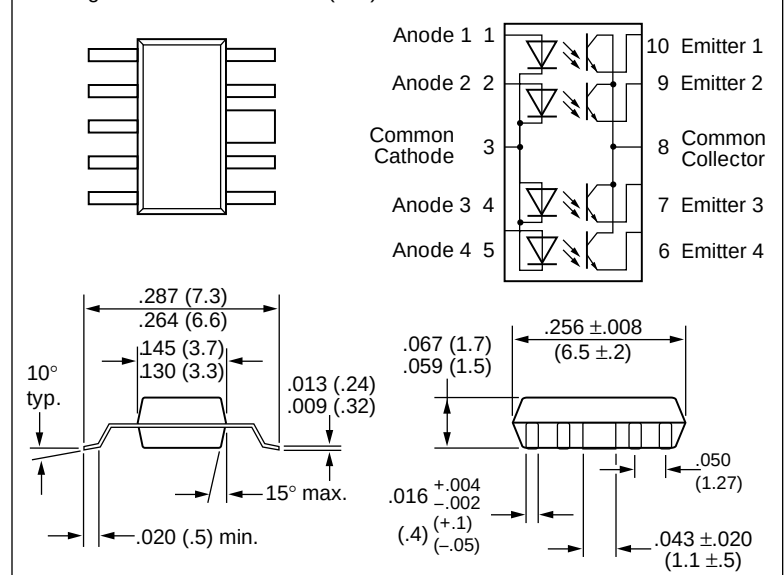
APPLICATIONS

- Telecommunication
- SMT
- PCMCIA
- Instrumentation

DESCRIPTION

The SFH6941 is a four channel mini-optocoupler suitable for high density packaged PCB application. It has a minimum of 2500 VDC isolation from input to output. The device consists of four phototransistors as detectors. Each channel is individually controlled. The optocoupler is housed in a SOT223 package. All the cathodes of the input LEDs and all the collectors of the output transistors are commoned enabling a pin count reduction from 16 pins to 10 pins—a significant space savings as compared to four channels that are electrically isolated individually.

Package Dimensions in Inches (mm)

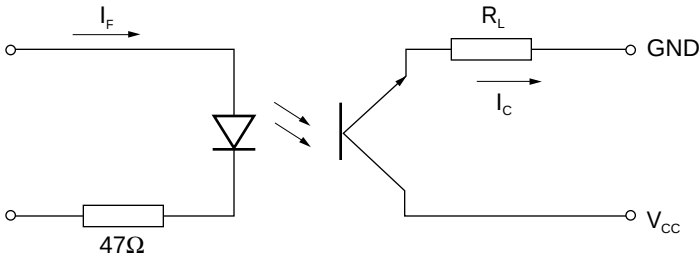


Characteristics (T_A=25°C, unless otherwise specified)

Description	Symbol	Min.	Typ.	Max.	Unit
Emitter (IR GaAs)					
Forward Voltage, I _F =5 mA	V _F		1.25		V
Reverse Current, V _R =3 V	I _R		0.01	10	μA
Capacitance, V _R =0 V, f=1 MHz	C ₀		5		pF
Thermal Resistance	R _{thJA}		1000		°K/W
Detector (Si Phototransistor)					
Collector-Emitter Voltage, I _{CE} =10 μA	V _{CEO}	70			V
Emitter-Collector Voltage, I _{EC} =10 μA	V _{ECO}	7			V
Capacitance, V _{CE} =5 V, f=1 MHz	C _{CE}		6		pF
Thermal Resistance	R _{thJA}		500		°K/W
Package					
Coupling Capacitance	C _C		1		pF

Description	Symbol	Values			Unit
		-3	-4	-5	
Coupling Transfer Ratio I _F =1 mA, V _{CE} =0.5 V I _F =0.5 mA, V _{CE} =1.5 V	I _C / I _F I _C / I _F	100–200 120 (≥50)	160–320 200 (≥80)	250–500 300 (≥125)	%
Collector-Emitter Saturation Voltage I _F =1 mA	V _{CEsat}	0.25 (≤0.4) (I _C =0.5 mA)	0.25 (≤0.4) (I _C =0.8 mA)	0.25 (≤0.4) (I _C =1.25 mA)	V
Collector-Emitter Leakage Current V _{CE} =10 V	I _{CEO}	50	50	50	nA

Switching times, typical



Description	Symbol	Values	Unit	Test Conditions
Turn-on Time	t _{on}	3	μs	I _F =2 mA R _L =100 Ω T _A =25°C V _{CC} =5 V
Rise Time	t _r	2.6		
Turn-off Time	t _{off}	3.1		
Fall Time	t _f	2.8		

Figure 1. LED current versus LED voltage $V_F=f(I_F)$

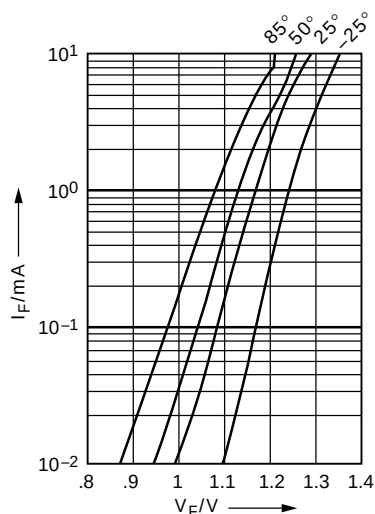


Figure 2. Saturated current transfer ratio normalized to $I_F=1$ mA, $NC-TR=f(I_F)$

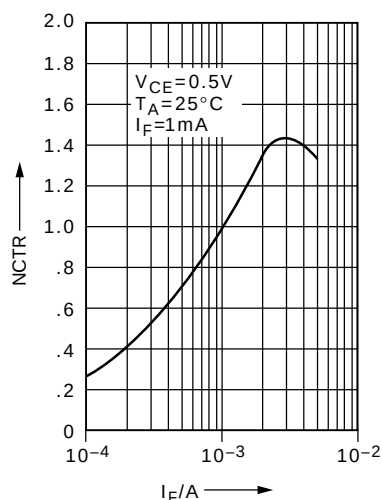


Figure 3. Non-saturated current transfer normalized to $I_F=1$ mA, $NC-TR=f(I_F)$

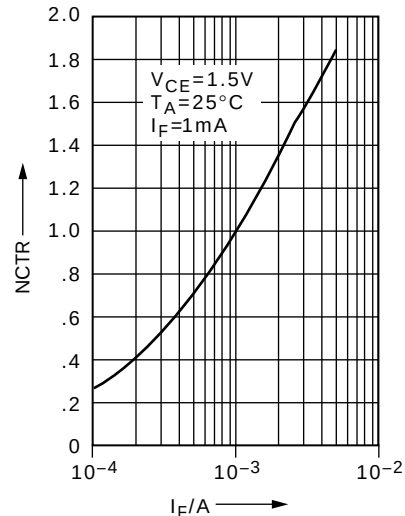


Figure 4. Transistor output characteristics $T_A=25^\circ\text{C}$, $I_{CE}=f(V_{CE}, I_F)$

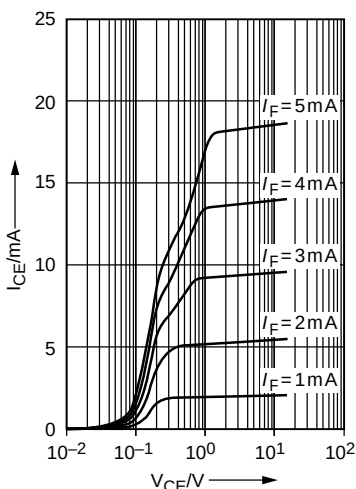


Figure 5. Transistor capacitance (typ.) $T_A=25^\circ\text{C}$, $f=1\text{MHz}$, $C_{CE}=f(V_{CE})$

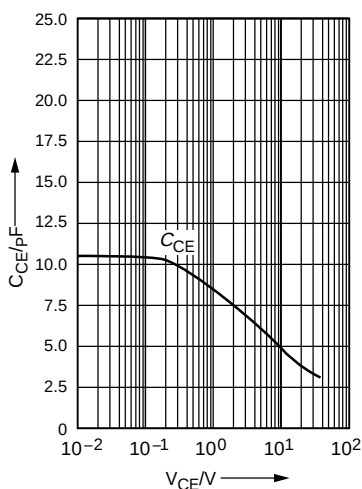


Figure 6. Collector-emitter leakage-current (typ.) $I_F=0$, $T_A=25^\circ\text{C}$, $I_{CEO}=f(V_{CE})$

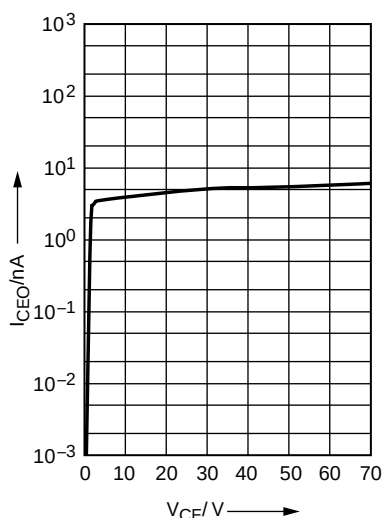


Figure 7. Permissible forward current diode $I_F=f(T_A=25^\circ\text{C})$

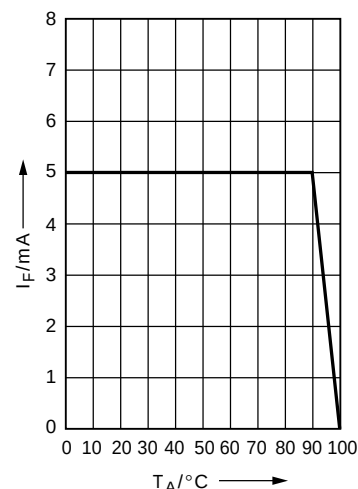


Figure 8. Permissible power dissipation $P_{tot}=f(T_A)$

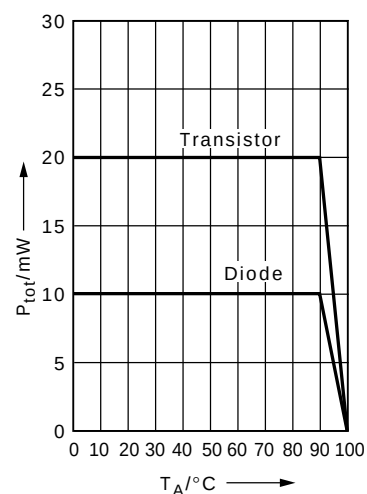


Figure 9. $T_A=25^\circ\text{C}$, $I_F=1$ mA, $V_{CC}=5$ V, t_{on} , t_r , t_{off} , $t_f=f(R_L)$

